

# Pavel A Yunin

## List of Publications by Citations

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117  
papers

495  
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12  
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15  
g-index

118  
ext. papers

567  
ext. citations

1.3  
avg, IF

3.53  
L-index

#	Paper	IF	Citations
117	Homoepitaxial growth of CVD diamond after ICP pretreatment. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 2572-2577	1.6	25
116	Sputter depth profiling of Mo/B <sub>4</sub> C/Si and Mo/Si multilayer nanostructures: A round-robin characterization by different techniques. <i>Thin Solid Films</i> , <b>2013</b> , 540, 96-105	2.2	21
115	Monolithically integrated InGaAs/GaAs/AlGaAs quantum well laser grown by MOCVD on exact Ge/Si(001) substrate. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 061111	3.4	19
114	Impact of growth and annealing conditions on the parameters of Ge/Si(001) relaxed layers grown by molecular beam epitaxy. <i>Semiconductors</i> , <b>2015</b> , 49, 1415-1420	0.7	18
113	GaAs/Ge/Si epitaxial substrates: Development and characteristics. <i>AIP Advances</i> , <b>2017</b> , 7, 015304	1.5	17
112	Copper(II)mercurium(III) 15-metallacrown-5 based on glycinehydroxamic acid as a new precursor for heterobimetallic composite materials on carbon nanotubes. <i>Polyhedron</i> , <b>2016</b> , 114, 96-100	2.7	15
111	Towards the indium nitride laser: obtaining infrared stimulated emission from planar monocrystalline InN structures. <i>Scientific Reports</i> , <b>2018</b> , 8, 9454	4.9	15
110	Characterization of interfaces in mosaic CVD diamond crystal. <i>Journal of Crystal Growth</i> , <b>2016</b> , 442, 62-67.	1.6	14
109	Recovery of SIMS depth profiles with account for nonstationary effects. <i>Applied Surface Science</i> , <b>2014</b> , 307, 33-41	6.7	13
108	Experimental shift allowance in the deconvolution of SIMS depth profiles. <i>Surface and Interface Analysis</i> , <b>2013</b> , 45, 1228-1232	1.5	13
107	The role of ultra-thin carbon barrier layers for fabrication of La/B <sub>4</sub> C interferential mirrors: Study by time-of-flight secondary ion mass spectrometry and high-resolution transmission electron microscopy. <i>Thin Solid Films</i> , <b>2015</b> , 577, 11-16	2.2	13
106	YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> long Josephson junctions on bicrystal Zr <sub>1-x</sub> Y <sub>x</sub> O <sub>2</sub> substrates fabricated by preliminary topology masks. <i>Superconductor Science and Technology</i> , <b>2017</b> , 30, 025007	3.1	12
105	Graft and block copolymers of chitosan with vinyl monomers: Synthesis, structure, and properties. <i>Polymer Science - Series B</i> , <b>2015</b> , 57, 93-105	0.8	12
104	Features of spectral properties of Sm(3+) complexes with dithia- and diselenophosphinate ligands. <i>Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy</i> , <b>2016</b> , 163, 134-9	4.4	12
103	A new approach to express ToF SIMS depth profiling. <i>Surface and Interface Analysis</i> , <b>2015</b> , 47, 771-776	1.5	11
102	Kinetics and formation mechanism of yttrium aluminum garnet from an amorphous phase prepared by the sol-gel method. <i>Ceramics International</i> , <b>2015</b> , 41, 10616-10623	5.1	10
101	Phase transitions in hybrid SFS structures with thin superconducting layers. <i>JETP Letters</i> , <b>2016</b> , 104, 329-333	1.3	9

100	MOCVD Growth of InGaAs/GaAs/AlGaAs Laser Structures with Quantum Wells on Ge/Si Substrates. <i>Crystals</i> , <b>2018</b> , 8, 311	2.3	9
99	New hybrid material based on multiwalled carbon nanotubes decorated with rhenium nanoparticles. <i>Journal of Surface Investigation</i> , <b>2015</b> , 9, 694-698	0.5	8
98	A study of planar structures formed on the modified Al <sub>2</sub> O <sub>3</sub> surfaces determining the topology of superconducting elements during YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-δ</sub> deposition. <i>Technical Physics Letters</i> , <b>2016</b> , 42, 594-597	0.7	8
97	Pyrolytic deposition of nanostructured titanium carbide coatings on the surface of multiwalled carbon nanotubes. <i>Technical Physics Letters</i> , <b>2016</b> , 42, 517-519	0.7	8
96	Depth profiling of fullerene-containing structures by time-of-flight secondary ion mass spectrometry. <i>Technical Physics Letters</i> , <b>2013</b> , 39, 1097-1100	0.7	8
95	Peculiarities in magnetron sputtering of YBCO epitaxial films for applications in superconductor electronics devices. <i>Technical Physics</i> , <b>2015</b> , 60, 1682-1688	0.5	8
94	A new approach to the diagnostics of nanoislands in Ge x Si <sub>1-x</sub> /Si heterostructures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , <b>2014</b> , 40, 601-605	0.7	7
93	Terahertz radiation from bismuth surface induced by femtosecond laser pulses. <i>Optics Letters</i> , <b>2016</b> , 41, 4289-92	3	7
92	Thin single-crystal Ge layers on Si substrates. <i>Technical Physics Letters</i> , <b>2015</b> , 41, 36-39	0.7	6
91	Grazing incidence mirrors with enhanced reflectance in the soft X-ray region. <i>Thin Solid Films</i> , <b>2016</b> , 598, 156-160	2.2	6
90	Si <sub>3</sub> N <sub>4</sub> layers for the in-situ passivation of GaN-based HEMT structures. <i>Semiconductors</i> , <b>2015</b> , 49, 1421-1424	0.7	6
89	The Gas-Phase Synthesis of a New Functional Hybrid Material on the Basis of Multiwalled Carbon Nanotubes Decorated with Faceted Aluminum Nanocrystals. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 865-868	0.7	6
88	Influence of thermal annealing on the electrical and luminescent properties of heavily Sb-doped Ge/Si(001) layers. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 124019	1.8	6
87	InN Layers Grown by MOCVD on a-Plane Al <sub>2</sub> O <sub>3</sub> . <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1700919	1.6	5
86	Hydrogen reduction of 98MoF <sub>6</sub> in RF discharge. <i>Journal of Radioanalytical and Nuclear Chemistry</i> , <b>2016</b> , 309, 833	1.5	5
85	Quantitative calibration and germanium SIMS depth profiling in Ge x Si <sub>1-x</sub> /Si heterostructures. <i>Semiconductors</i> , <b>2014</b> , 48, 1109-1117	0.7	5
84	Peculiarities of growing InGaAs/GaAs/AlGaAs laser structures by MOCVD on Ge/Si substrates. <i>Semiconductors</i> , <b>2017</b> , 51, 1527-1530	0.7	5
83	Method for taking into account the shift parameter in the deconvolution of the depth composition distribution of semiconductor structures from SIMS depth profiles. <i>Semiconductors</i> , <b>2012</b> , 46, 1481-1486	0.7	5

82	Quantitative depth profiling of Si <sub>1-x</sub> Ge <sub>x</sub> structures by time-of-flight secondary ion mass spectrometry and secondary neutral mass spectrometry. <i>Thin Solid Films</i> , <b>2016</b> , 607, 25-31	2.2	5
81	Synthesis and properties of chitosan-poly lactide compositions produced with the use of compatibilizers. <i>Polymer Science - Series B</i> , <b>2015</b> , 57, 239-243	0.8	4
80	Electrical conductivity of vacuum deposited films and crystals of redox-isomeric $\beta$ -semiquinonato cobalt complexes. <i>Solid State Sciences</i> , <b>2015</b> , 48, 13-18	3.4	4
79	Synchrotron, X-Ray, and Electron Microscopic Studies of Catalyst Systems Based on Multiwalled Carbon Nanotubes Modified by Copper Nanoparticles. <i>Physics of the Solid State</i> , <b>2020</b> , 62, 214-222	0.8	4
78	Raman spectra of amorphous isotope-enriched <sup>74</sup> Ge with low-strained Ge nanocrystals. <i>Thin Solid Films</i> , <b>2014</b> , 552, 46-49	2.2	4
77	Study of multilayered SiGe semiconductor structures by X-ray diffractometry, grazing-incidence X-ray reflectometry, and secondary-ion mass spectrometry. <i>Semiconductors</i> , <b>2013</b> , 47, 1556-1561	0.7	4
76	Matched characterization of super-multi-period superlattices. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 455103	3	4
75	Features of InN growth by nitrogen-plasma-assisted MBE at different ratios of fluxes of group-III and -V elements. <i>Semiconductors</i> , <b>2016</b> , 50, 261-265	0.7	4
74	Study of the Structural and Morphological Properties of HPHT Diamond Substrates. <i>Semiconductors</i> , <b>2018</b> , 52, 1432-1436	0.7	4
73	Plasma-Chemical Deposition of Diamond-Like Films onto the Surface of Heavily Doped Single-Crystal Diamond. <i>Semiconductors</i> , <b>2019</b> , 53, 1203-1206	0.7	3
72	Phase Diagrams of Thin Disordered Films Based on HTSC YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> in External Magnetic Fields. <i>Physics of the Solid State</i> , <b>2019</b> , 61, 1523-1528	0.8	3
71	On the use of an external reference sample in the X-ray diffraction analysis of epitaxial layers. <i>Journal of Surface Investigation</i> , <b>2016</b> , 10, 96-100	0.5	3
70	Use of related parameters in X-ray diffraction analysis of multilayer structures with allowance for the layer growth time. <i>Technical Physics</i> , <b>2014</b> , 59, 402-406	0.5	3
69	A new alternative to secondary CsM <sup>+</sup> ions for depth profiling of multilayer metal structures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , <b>2013</b> , 39, 46-50	0.7	3
68	Growth of light-emitting SiGe heterostructures on strained silicon-on-insulator substrates with a thin oxide layer. <i>Semiconductors</i> , <b>2015</b> , 49, 1104-1110	0.7	3
67	Continuous monitoring of temperature and rate of plasma etching of semiconductor wafers. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 111601	3.4	3
66	Growth and formation of the microstructure of YBCO films deposited by magnetron sputtering on fianite substrates. <i>Technical Physics</i> , <b>2014</b> , 59, 1487-1491	0.5	3
65	Monocrystalline InN Films Grown at High Rate by Organometallic Vapor Phase Epitaxy with Nitrogen Plasma Activation Supported by Gyrotron Radiation. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 110201	1.4	3

64	SIMS Analysis of Carbon-Containing Materials: Content of Carbon Atoms in sp <sup>2</sup> and sp <sup>3</sup> Hybridization States. <i>Technical Physics Letters</i> , <b>2020</b> , 46, 290-294	0.7	3
63	Formation of singular (001) terraces on the surface of single-crystal HPHT diamond substrates. <i>Semiconductors</i> , <b>2016</b> , 50, 1622-1625	0.7	3
62	A Study of the Isolation Region of Planar Superconducting YBCO Structures Formed by the Master Mask Method. <i>Physics of the Solid State</i> , <b>2018</b> , 60, 2139-2144	0.8	3
61	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. <i>Semiconductors</i> , <b>2018</b> , 52, 1547-1550	0.7	3
60	Misorientation Angle Dependence of Boron Incorporation Into CVD Diamond Delta Layers. <i>Physica Status Solidi (B): Basic Research</i> , <b>2019</b> , 256, 1800606	1.3	2
59	Raman spectroscopy of InGaAs/GaAs nanoheterostructures doped with Mn. <i>Semiconductors</i> , <b>2015</b> , 49, 99-103	0.7	2
58	Heavily doped GaAs:Te layers grown by MOVPE using diisopropyl telluride as a source. <i>Semiconductors</i> , <b>2016</b> , 50, 1439-1442	0.7	2
57	Emission Properties of Heavily Doped Epitaxial Indium-Nitride Layers. <i>Semiconductors</i> , <b>2019</b> , 53, 1357-1362	0.7	2
56	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. <i>Technical Physics Letters</i> , <b>2015</b> , 41, 648-650	0.7	2
55	New approach to the X-ray diffraction analysis of test structures during flow calibration in epitaxial growth reactors. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 494-497	0.5	2
54	Application of a pseudomorphous layer on a vicinal substrate as a test sample for high-resolution X-ray diffractometry. <i>Journal of Surface Investigation</i> , <b>2015</b> , 9, 1243-1250	0.5	2
53	Layer-by-layer analysis of structures containing $\delta$ layers by secondary ion mass spectrometry taking into account the TOF-SIMS-5 depth resolution function. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 574-577	0.5	2
52	Analysis of the composition of (Al,Ga)As alloys by secondary ion mass spectroscopy and X-ray diffractometry. <i>Semiconductors</i> , <b>2012</b> , 46, 1392-1395	0.7	2
51	Direct comparison of superlattice periods measured with X-ray diffractometry and optical interferometry. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , <b>2011</b> , 75, 40-43	0.4	2
50	Carbon Films Produced by the Pulsed Laser Method and Their Influence on the Properties of GaAs Structures. <i>Semiconductors</i> , <b>2020</b> , 54, 1059-1063	0.7	2
49	Modification of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> thin films by ion implantation. <i>Journal of Surface Investigation</i> , <b>2016</b> , 10, 438-440	0.5	2
48	Nonlinear calibration curves in secondary ion mass spectrometry for quantitative analysis of gesi heterostructures with nanoclusters. <i>Technical Physics Letters</i> , <b>2016</b> , 42, 243-247	0.7	2
47	Influence of Thermal Annealing on the Properties of Multilayer Mo/Be Mirrors. <i>Technical Physics</i> , <b>2019</b> , 64, 1692-1697	0.5	2

46	Comparative Analysis of the Luminescence of Ge:Sb Layers Grown on Ge(001) and Si(001) Substrates. <i>Semiconductors</i> , <b>2019</b> , 53, 1318-1323	0.7	1
45	Structural and optical properties of GaAsSb QW heterostructures grown by laser deposition. <i>Semiconductors</i> , <b>2015</b> , 49, 109-112	0.7	1
44	High-rate growth of InN films on sapphire and sapphire substrates by metalorganic vapor phase epitaxy with plasma-assisted nitrogen activation. <i>Technical Physics Letters</i> , <b>2015</b> , 41, 266-269	0.7	1
43	Synthesis of Hybrid Materials Based on Iron Nanoparticle-Decorated Multiwalled Carbon Nanotubes. <i>Inorganic Materials</i> , <b>2018</b> , 54, 233-236	0.9	1
42	High-coercivity magnetic mirror polarizers for thermal neutrons. <i>Journal of Surface Investigation</i> , <b>2016</b> , 10, 486-489	0.5	1
41	Influence of the Rotation Frequency of a Disk Substrate Holder on the Crystal Structure Characteristics of MOCVD-Grown GaAs Layers. <i>Technical Physics</i> , <b>2018</b> , 63, 211-215	0.5	1
40	Grazing Incidence X-Ray Diffraction Study of Tantalum Thin Films. <i>Journal of Surface Investigation</i> , <b>2018</b> , 12, 701-704	0.5	1
39	New Hybrid Material Based on Multiwalled Carbon Nanotubes Decorated by Rhenium-Tungsten Nanodendrites. <i>Journal of Surface Investigation</i> , <b>2018</b> , 12, 682-687	0.5	1
38	Changes in the elemental composition and microstructure of an YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> target during magnetron sputtering. <i>Technical Physics Letters</i> , <b>2013</b> , 39, 862-865	0.7	1
37	Investigation of X-ray diffraction limitations upon the analysis of tellurium-atom injection into GaAs epitaxial layers. <i>Journal of Surface Investigation</i> , <b>2017</b> , 11, 361-365	0.5	1
36	Possibilities of the Master Mask Method in Analysis of Characteristics of Planar HTSC Structures Depending on Superconducting Film Thickness. <i>Technical Physics</i> , <b>2020</b> , 65, 1605-1608	0.5	1
35	Small-molecule heterojunctions: Stability to ageing under sunlight. <i>Applied Surface Science</i> , <b>2022</b> , 578, 152084	6.7	1
34	Low-barrier Mott diodes with near-surface polarization-induced doping. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 013505	3.4	1
33	Near-infrared stimulated emission from indium-rich InGaN layers grown by plasma-assisted MBE. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 151902	3.4	1
32	Influence of surface roughness on a change in the growth mode from two-dimensional to three-dimensional for strained SiGe heterostructures. <i>Semiconductors</i> , <b>2016</b> , 50, 1630-1634	0.7	1
31	Pulsed Ion-Beam Treatment of Germanium Implanted by Antimony Ions. <i>Optoelectronics, Instrumentation and Data Processing</i> , <b>2019</b> , 55, 423-430	0.6	1
30	Magnetostriction Effect in Ferromagnetic Films with Easy-Axis and Easy-Plane Anisotropies. <i>Technical Physics</i> , <b>2019</b> , 64, 1646-1651	0.5	1
29	Investigation of the Anisotropy of the Structural Properties of GaN(0001) Layers Grown by MOVPE on a-Plane (11 $\bar{2}$ ) <sub>0</sub> Sapphire. <i>Semiconductors</i> , <b>2018</b> , 52, 1412-1415	0.7	1

28	Plasma Chemical Etching of Gallium Arsenide in C2F5Cl-Based Inductively Coupled Plasma. <i>Semiconductors</i> , <b>2018</b> , 52, 1473-1476	0.7	1
27	A New Limitation of the Depth Resolution in TOF-SIMS Elemental Profiling: the Influence of a Probing Ion Beam. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 320-323	0.7	1
26	A Comparative Analysis of Catalysts for the Preparation of Germanium through Hydrogen Reduction of Germanium Tetrachloride. <i>Inorganic Materials</i> , <b>2018</b> , 54, 971-976	0.9	1
25	New Cluster Secondary Ions for Quantitative Analysis of the Concentration of Boron Atoms in Diamond by Time-of-Flight Secondary-Ion Mass Spectrometry. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 297-300	0.7	1
24	Nanostructuring of Mn(II)Pc thin films by vacuum deposition in a weak magnetic field. <i>Vacuum</i> , <b>2021</b> , 194, 110584	3.7	1
23	Effect of the AlGaAs Seed Layer Composition on Antiphase Domains Formation in (Al)GaAs Structures Grown by Vapor-Phase Epitaxy on Ge/Si(100) Substrates. <i>Technical Physics Letters</i> , <b>2021</b> , 47, 413-416	0.7	1
22	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 165701	2.5	0
21	Epitaxial GaN layers formed on langasite substrates by the plasma-assisted MBE method. <i>Semiconductors</i> , <b>2016</b> , 50, 1511-1514	0.7	0
20	Selective analysis of the elemental composition of InGaAs/GaAs nanoclusters by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , <b>2017</b> , 43, 477-480	0.7	0
19	Low-temperature deposition of SiN <sub>x</sub> Films in SiH <sub>4</sub> /Ar + N <sub>2</sub> inductively coupled plasma under high silane dilution with argon. <i>Semiconductors</i> , <b>2017</b> , 51, 1449-1452	0.7	0
18	The Microstructure of Transition Boundaries in Multilayer Mo/Be Systems. <i>Technical Physics</i> , <b>2020</b> , 65, 1800-1808	0.5	0
17	Ion-Beam Synthesis of Gallium Oxide Nanocrystals in a SiO <sub>2</sub> /Si Dielectric Matrix. <i>Nanomaterials</i> , <b>2022</b> , 12, 1840	5.4	0
16	Microwave Impedance of Thin-Film Superconductor/Normal Metal Hybrid Structures with a High Conductivity Ratio. <i>Physics of the Solid State</i> , <b>2019</b> , 61, 1675-1681	0.8	
15	Microstructure and Density of Mo Films in Multilayer Mo/Si Mirrors. <i>Journal of Surface Investigation</i> , <b>2019</b> , 13, 8-13	0.5	
14	Plastic relaxation in GeSi layers on Si (001) and Si (115) substrates. <i>Semiconductors</i> , <b>2015</b> , 49, 19-22	0.7	
13	Extremely deep profiling analysis of the atomic composition of thick (>100 nm) GaAs layers within power PIN diodes by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , <b>2016</b> , 42, 783-787	0.7	
12	Stimulated emission from a metamorphic GaAsSb bulk layer on a GaAs substrate. <i>Semiconductors</i> , <b>2016</b> , 50, 586-589	0.7	
11	Specific features of the photoexcitation spectra of epitaxial InN layers grown by molecular-beam epitaxy with the plasma activation of nitrogen. <i>Semiconductors</i> , <b>2017</b> , 51, 1537-1541	0.7	

- 10 Single-crystal GaN/AlN layers on CVD diamond. *Technical Physics Letters*, **2015**, 41, 954-956 0.7
- 9 Terahertz-range spontaneous emission under the optical excitation of donors in uniaxially stressed bulk silicon and SiGe/Si heterostructures. *Semiconductors*, **2015**, 49, 13-18 0.7
- 8 Coulomb centers assisted tunneling in a doped triple barrier SiGe heterostructure. *Physica E: Low-Dimensional Systems and Nanostructures*, **2014**, 57, 42-46 3
- 7 Experimental Observation of s-Component of Superconducting Pairing in Thin Disordered HTSC Films Based on YBCO. *Physics of the Solid State*, **2020**, 62, 1598-1603 0.8
- 6 Atomic Force Microscopy Examination of Elementary Processes in Metalorganic Compound Hydride Epitaxy of GaAs-Based Nanoheterostructures. *Technical Physics*, **2020**, 65, 791-794 0.5
- 5 The Magnetoelectric Effect in Ferroelectric/Ferromagnetic Film Hybrid Systems with Easy-Plane and Easy-Axis Anisotropy. *Technical Physics*, **2020**, 65, 1832-1836 0.5
- 4 Modification of the Ratio between sp<sup>2</sup>- to sp<sup>3</sup>-Hybridized Carbon Components in PECVD Diamond-Like Films. *Semiconductors*, **2020**, 54, 1047-1050 0.7
- 3 Formation of Ohmic Contacts to a Diamond-Like Carbon Layer Deposited on a Dielectric Diamond Substrate. *Semiconductors*, **2020**, 54, 1056-1058 0.7
- 2 Verification of the Hypothesis on the Thermoelastic Nature of Deformation of a (0001)GaN Layer Grown on the Sapphire a-Cut. *Semiconductors*, **2018**, 52, 1491-1494 0.7
- 1 Effect of the Chloropentafluoroethane Additive in Chlorine-Containing Plasma on the Etching Rate and Etching-Profile Characteristics of Gallium Arsenide. *Semiconductors*, **2021**, 55, 865-868 0.7